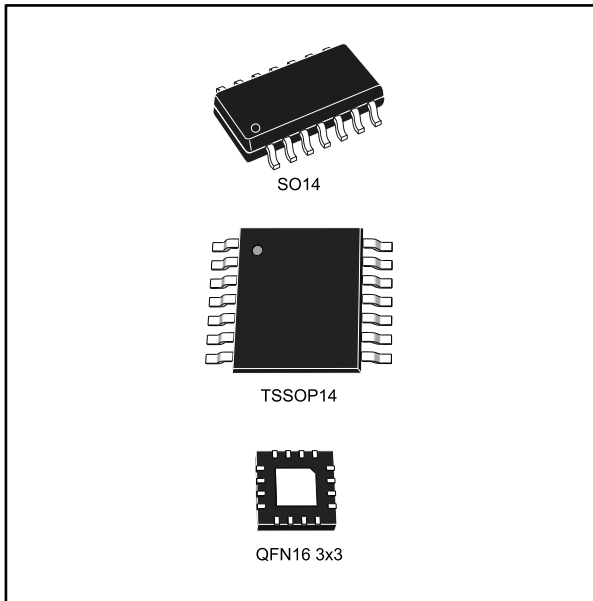


Low-power quad operational amplifiers

Datasheet - production data



Description

This circuit consists of four independent, high-gain operational amplifiers (op amps) which employ internal frequency compensation and are specifically designed for automotive and industrial control systems.

The device operates from a single power supply over a wide range of voltages. Operation from split power supplies is also possible and the low-power supply current drain is independent from the power supply voltage magnitude.

Features

- Wide gain bandwidth: 1.3 MHz
- Input common-mode voltage range includes negative rail
- Large voltage gain: 100 dB
- Supply current per amplifier: 375 μ A
- Low input bias current: 20 nA
- Low input offset current: 2 nA
- Wide power supply range:
 - Single supply: 3 V to 30 V
 - Dual supplies: ± 1.5 V to ± 15 V

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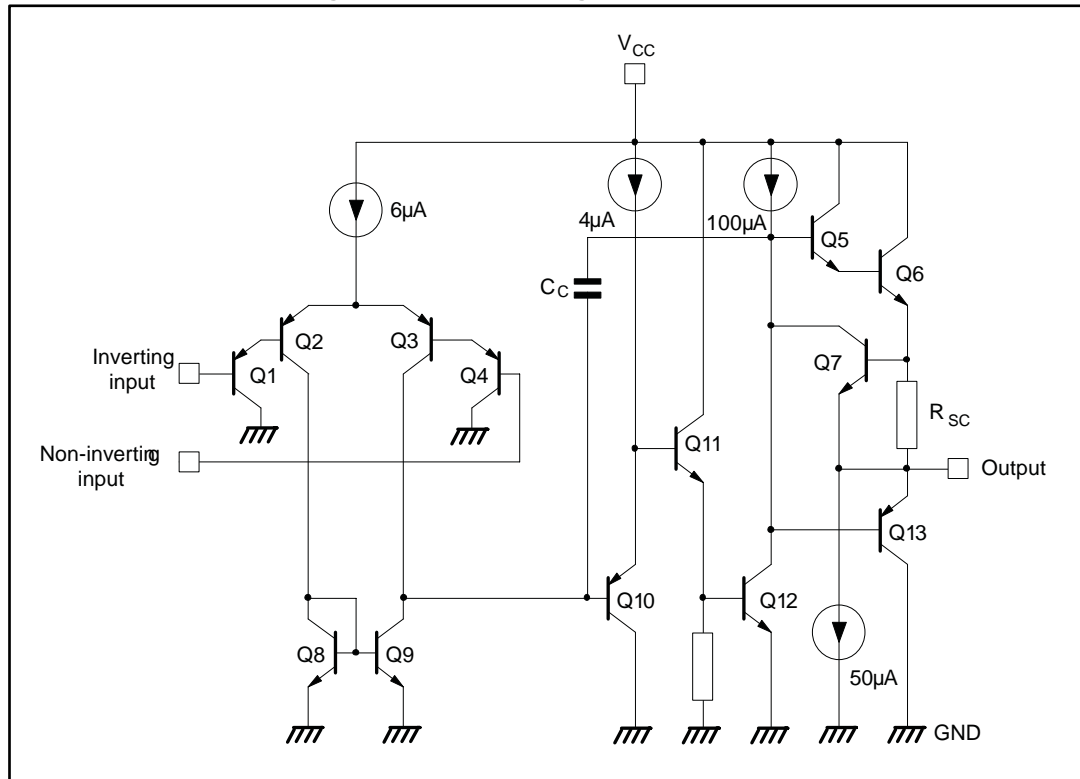
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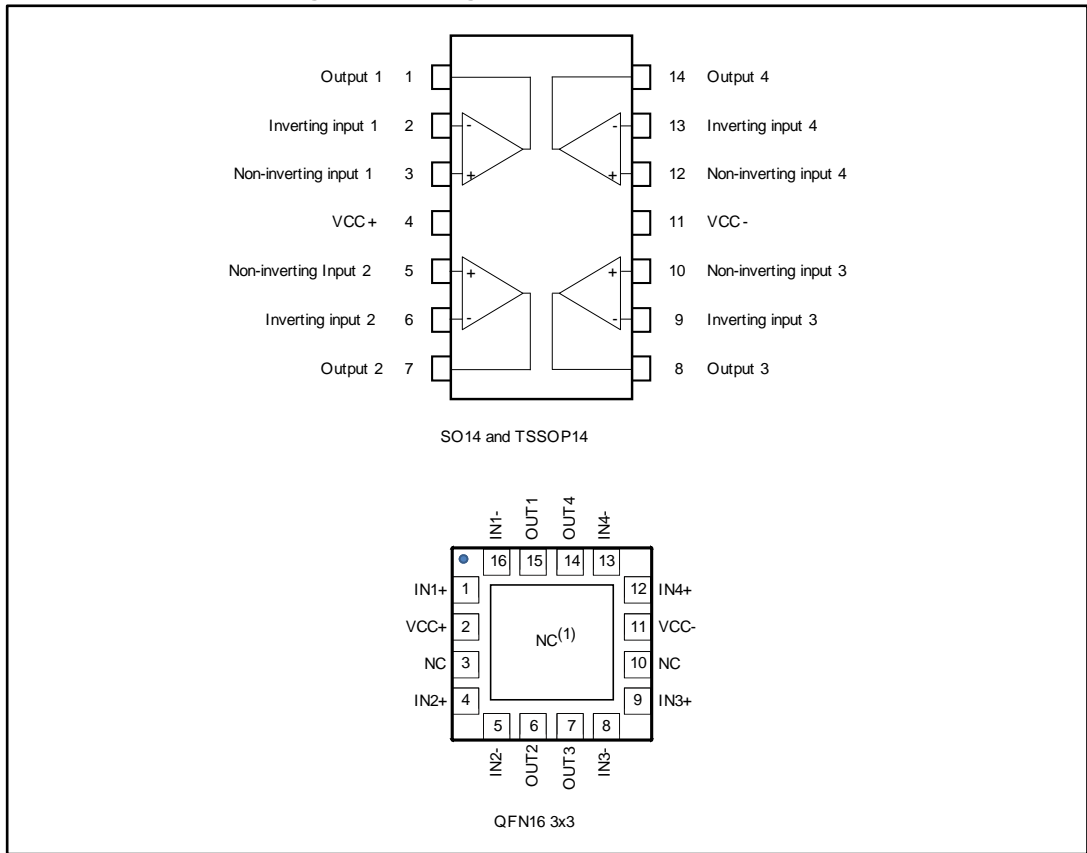
1 Schematic diagram

Figure 1: Schematic diagram (1/4 LM2902)



2 Pinout information

Figure 2: Package pin connections (top view)



1. The exposed pads of the QFN16 3x3 can be connected to VCC- or left floating.

3 Absolute maximum ratings and operating conditions

Table 1: Absolute maximum ratings (AMR)

Symbol	Parameter	Value	Unit	
V _{CC}	Supply voltage ⁽¹⁾	± 16 to 32	V	
V _{id}	Differential input voltage ⁽²⁾	32		
V _{in}	Input voltage	-0.3 to 32		
	Output short-circuit duration ⁽³⁾	Infinite	s	
T _j	Maximum junction temperature	150	° C	
T _{stg}	Storage temperature range	-65 to 150		
I _{in}	Input current : V _{in} driven negative ⁽⁴⁾	5 in DC or 50 in AC (duty cycle = 10 %, T = 1 s)	mA	
	Input current : V _{in} driven positive above AMR value ⁽⁵⁾	0.4		
R _{thja}	Thermal resistance junction-to-ambient ⁽⁶⁾	SO14	105	° C/W
		TSSOP14	100	
		QFN16 3x3	45	
R _{thjc}	Thermal resistance junction-to-case	SO14	31	
		TSSOP14	32	
		QFN16 3x3	14	
ESD	HBM: human body model ⁽⁷⁾	370	V	
	MM: machine model ⁽⁸⁾	150		
	CDM: charged device model ⁽⁹⁾	1500		

Notes:

⁽¹⁾All voltage values, except the differential voltage are with respect to the network ground terminal.

⁽²⁾Differential voltages are the non-inverting input terminal with respect to the inverting input terminal.

⁽³⁾Short-circuits from the output to V_{CC}⁺ can cause excessive heating and eventual destruction. The maximum output current is approximately 20 mA, independent of the magnitude of V_{CC}⁺.

⁽⁴⁾This input current only exists when the voltage at any of the input leads is driven negative. It is due to the collector-base junction of the input PNP transistor becoming forward-biased and thereby acting as an input diode clamp. In addition to this diode action, there is an NPN parasitic action on the IC chip. This transistor action can cause the output voltages of the op amps to go to the V_{CC} voltage level (or to ground for a large overdrive) for the time during which an input is driven negative. This is not destructive and normal output is restored for input voltages above -0.3 V.

⁽⁵⁾The junction base/substrate of the input PNP transistor polarized in reverse must be protected by a resistor in series with the inputs to limit the input current to 400 μ A max (R = (V_{in} - 36 V)/400 μ A).

⁽⁶⁾R_{thja/c} are typical values.

⁽⁷⁾Human body model: a 100 pF capacitor is charged to the specified voltage, then discharged through a 1.5 kΩ resistor between two pins of the device. This is done for all couples of connected pin combinations while the other pins are floating.

⁽⁸⁾Machine model: a 200 pF capacitor is charged to the specified voltage, then discharged directly between two pins of the device with no external series resistor (internal resistor < 5 Ω). This is done for all couples of connected pin combinations while the other pins are floating.

⁽⁹⁾Charged device model: all pins and the package are charged together to the specified voltage and then discharged directly to the ground through only one pin. This is done for all pins.

Table 2: Operating conditions

Symbol	Parameter	Value	Unit
V _{CC}	Supply voltage	3 to 30	V
V _{icm}	Common mode input voltage range	(V _{CC} ⁺) - 1.5	
		T _{min} ≤ T _{amb} ≤ T _{max} (V _{CC} ⁺) - 2	
T _{oper}	Operating free-air temperature range	-40 to 125	°C

4 Electrical characteristics

Table 3: $V_{CC+} = 5\text{ V}$, $V_{CC-} = \text{Ground}$, $V_O = 1.4\text{ V}$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$ (unless otherwise stated)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{iO}	Input offset voltage ⁽¹⁾	$T_{\text{amb}} = 25\text{ }^\circ\text{C}$		2	7	mV
		$T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$			9	
$\Delta V_{iO}/\Delta T$	Input offset voltage drift			7	30	$\mu\text{V}/^\circ\text{C}$
I_{iO}	Input offset current	$T_{\text{amb}} = 25\text{ }^\circ\text{C}$		2	30	nA
		$T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$			40	
DI_{iO}	Input offset current drift			10	200	$\text{pA}/^\circ\text{C}$
I_{iB}	Input bias current ⁽²⁾	$T_{\text{amb}} = 25\text{ }^\circ\text{C}$		20	150	nA
		$T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$			300	
A_{vd}	Large signal voltage gain	$V_{CC+} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_O = 1.4\text{ V to } 11.4\text{ V}$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	50	100		V/mV
		$V_{CC+} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_O = 1.4\text{ V to } 11.4\text{ V}$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	25			
SVR	Supply voltage rejection ratio	$R_S \leq 10\text{ k}\Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	65	110		dB
		$R_S \leq 10\text{ k}\Omega$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	65			
I_{CC}	Supply current, all op amps, no load	$T_{\text{amb}} = 25\text{ }^\circ\text{C}$, $V_{CC+} = 5\text{ V}$		0.7	1.2	mA
		$T_{\text{amb}} = 25\text{ }^\circ\text{C}$, $V_{CC+} = 30\text{ V}$		1.5	3	
		$T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$, $V_{CC+} = 5\text{ V}$		0.8	1.2	
		$T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$, $V_{CC+} = 30\text{ V}$		1.5	3	
CMR	Common-mode rejection ratio	$R_S \leq 10\text{ k}\Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	70	80		dB
		$R_S \leq 10\text{ k}\Omega$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	60			
I_O	Output short-circuit current	$V_{iD} = 1\text{ V}$, $V_{CC+} = 15\text{ V}$, $V_O = 2\text{ V}$	20	40	70	mA
I_{sink}	Output sink current	$V_{iD} = -1\text{ V}$, $V_{CC+} = 15\text{ V}$, $V_O = 2\text{ V}$	10	20		μA
		$V_{iD} = -1\text{ V}$, $V_{CC+} = 15\text{ V}$, $V_O = 0.2\text{ V}$	12	50		
V_{OH}	High-level output voltage	$V_{CC+} = 30\text{ V}$, $R_L = 2\text{ k}\Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	26	27		V
		$V_{CC+} = 30\text{ V}$, $R_L = 2\text{ k}\Omega$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	26			
		$V_{CC+} = 30\text{ V}$, $R_L = 10\text{ k}\Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	27	28		
		$V_{CC+} = 30\text{ V}$, $R_L = 10\text{ k}\Omega$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	27			
		$V_{CC+} = 5\text{ V}$, $R_L = 2\text{ k}\Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$	3			
		$V_{CC+} = 5\text{ V}$, $R_L = 2\text{ k}\Omega$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$	3.5			
V_{OL}	Low-level output voltage	$R_L = 10\text{ k}\Omega$, $T_{\text{amb}} = 25\text{ }^\circ\text{C}$		5	20	mV
		$R_L = 10\text{ k}\Omega$, $T_{\text{min}} \leq T_{\text{amb}} \leq T_{\text{max}}$			20	
SR	Slew rate	$V_{CC+} = 15\text{ V}$, $V_{in} = 0.5\text{ to } 3\text{ V}$, $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$, unity gain		0.4		$\text{V}/\mu\text{s}$
GBP	Gain bandwidth product	$V_{CC+} = 30\text{ V}$, $V_{in} = 10\text{ mV}$, $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$		1.3		MHz
THD	Total harmonic distortion	$f = 1\text{ kHz}$, $A_V = 20\text{ dB}$, $R_L = 2\text{ k}\Omega$, $V_O = 2\text{ V}_{pp}$, $C_L = 100\text{ pF}$, $V_{CC+} = 30\text{ V}$		0.015		%

Electrical characteristics

LM2902

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
e_n	Equivalent input noise voltage	$f = 1 \text{ kHz}, R_S = 100 \ \Omega, V_{CC^+} = 30 \text{ V}$		40		$\text{nV}/\sqrt{\text{Hz}}$
V_{O1}/V_{O2}	Channel separation ⁽³⁾	$1 \text{ kHz} \leq f \leq 20 \text{ kHz}$		120		dB

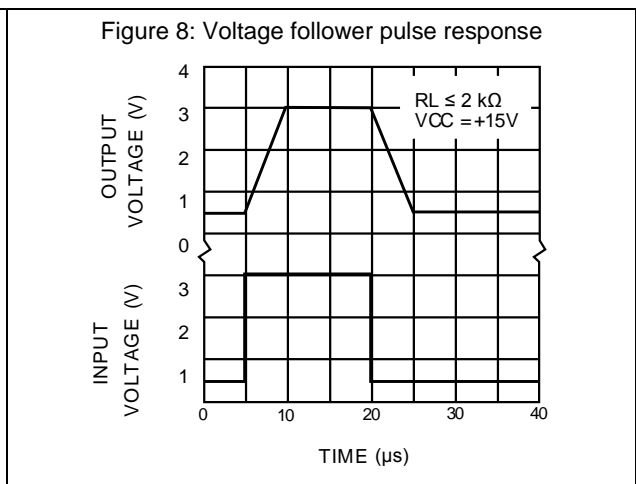
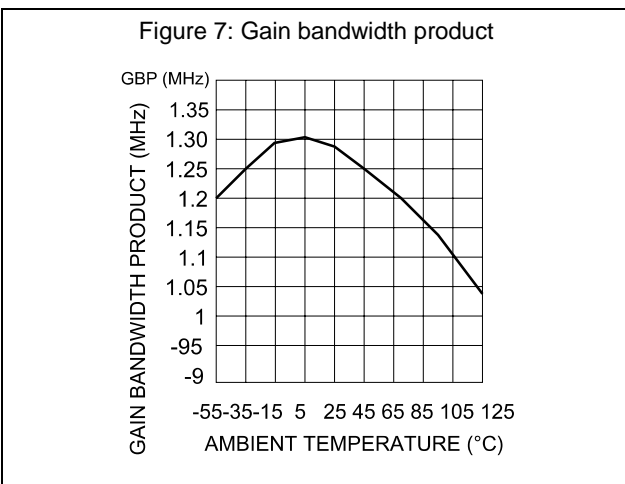
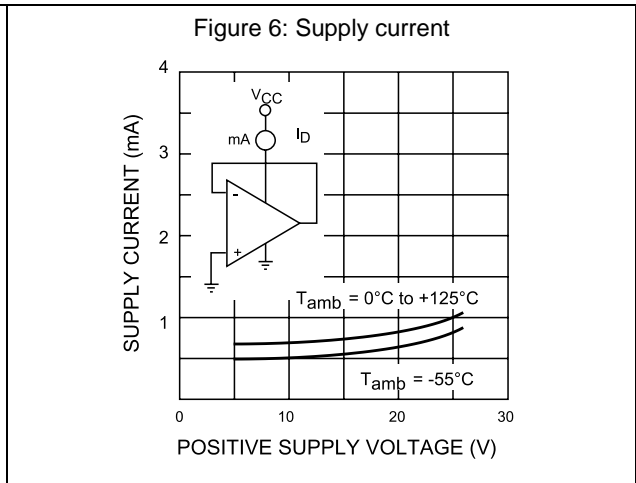
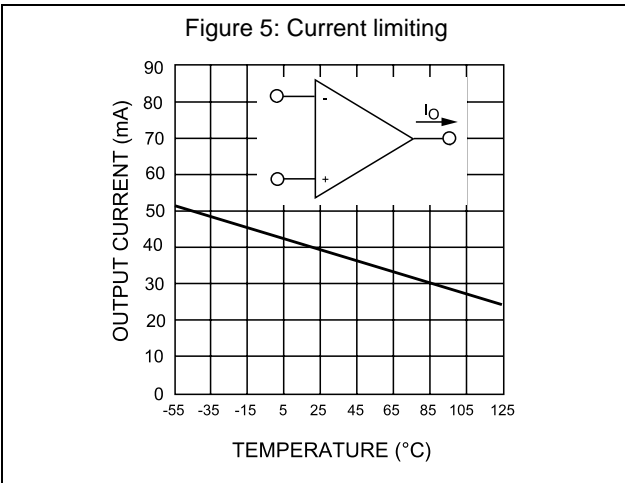
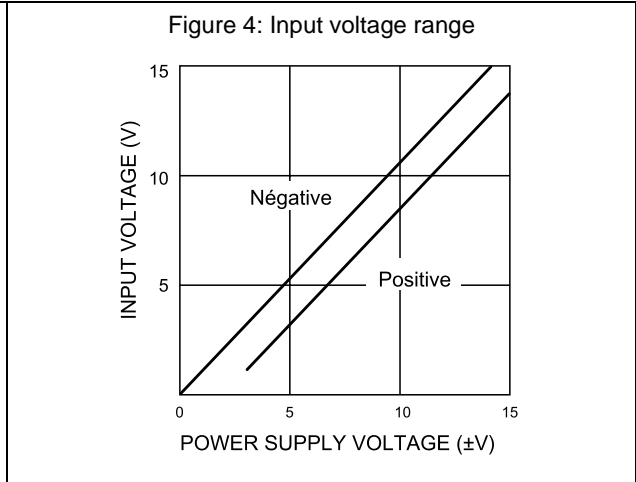
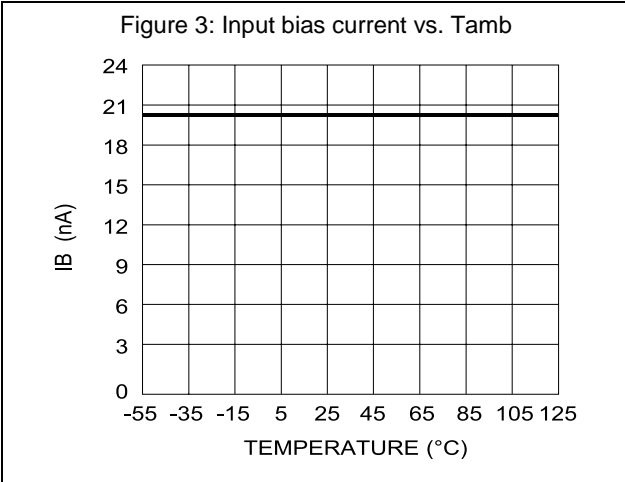
Notes:

⁽¹⁾ $V_O = 1.4 \text{ V}, R_S = 0 \ \Omega, 5 \text{ V} < V_{CC^+} < 30 \text{ V}, 0 \text{ V} < V_{ic} < (V_{CC^+}) - 1.5 \text{ V}.$

⁽²⁾The direction of the input current is out of the IC. This current is essentially constant, independent of the state of the output, so there is no change in the load on the input lines.

⁽³⁾Due to the proximity of external components, ensure that stray capacitance does not cause coupling between these external parts. Typically, this can be detected as this type of capacitance increases at higher frequencies.

5 Electrical characteristic curves



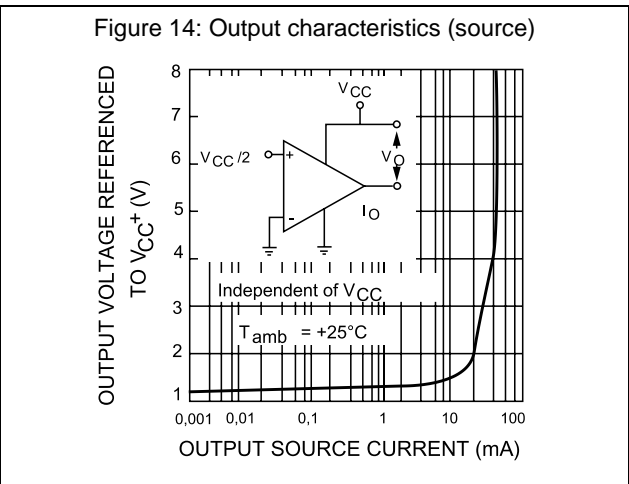
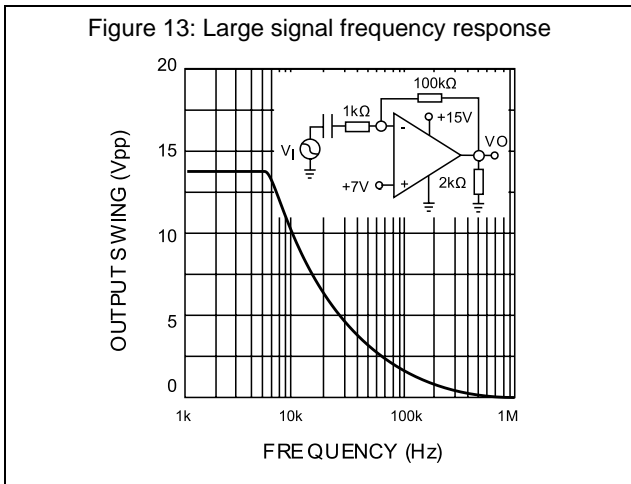
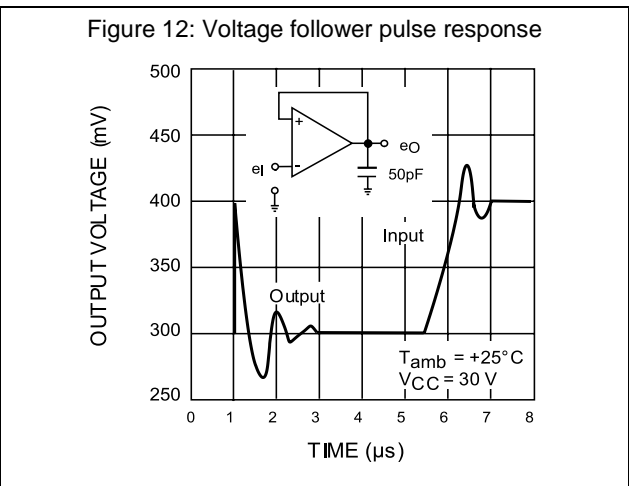
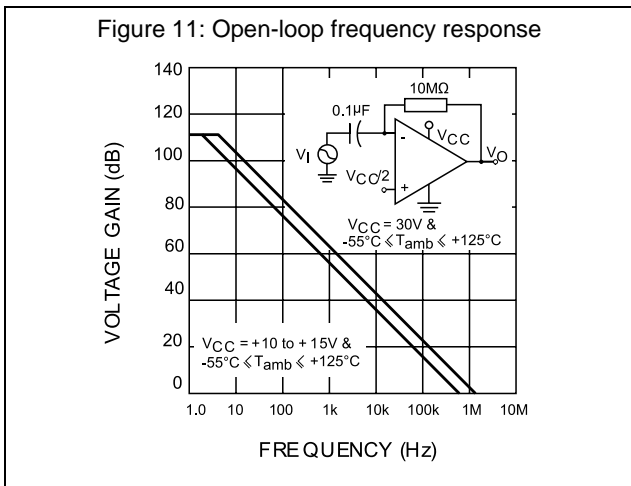
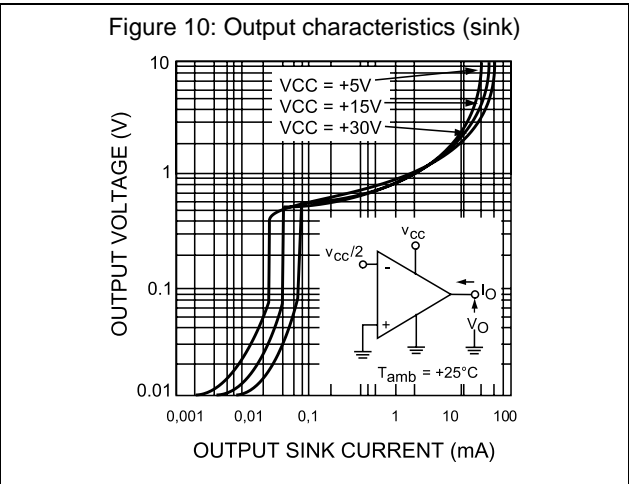
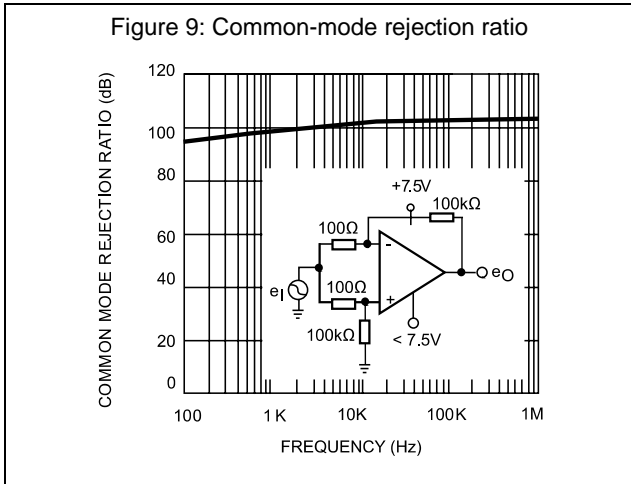


Figure 15: Input current

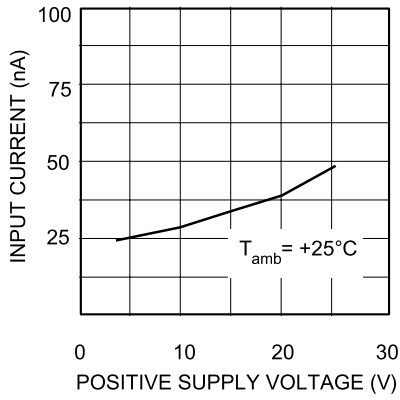


Figure 16: Voltage gain

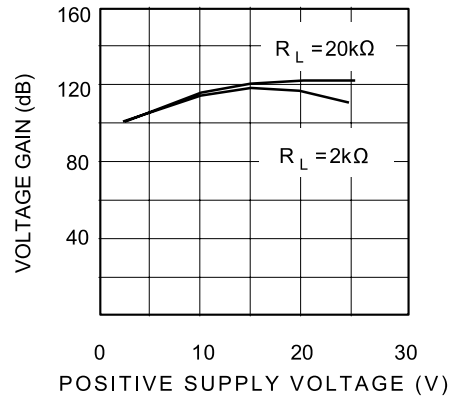


Figure 17: Power supply and common-mode rejection ratio

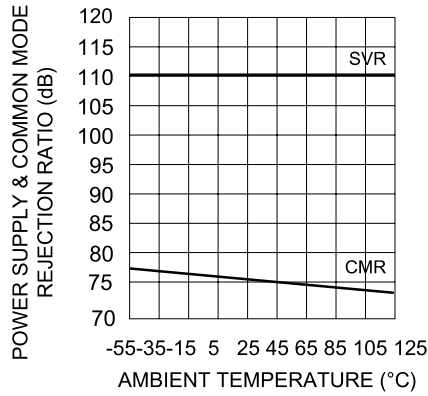
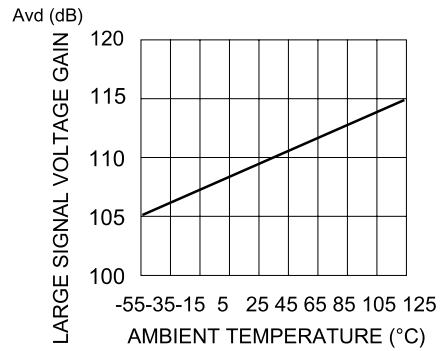


Figure 18: Large signal voltage gain



6 Typical single-supply applications

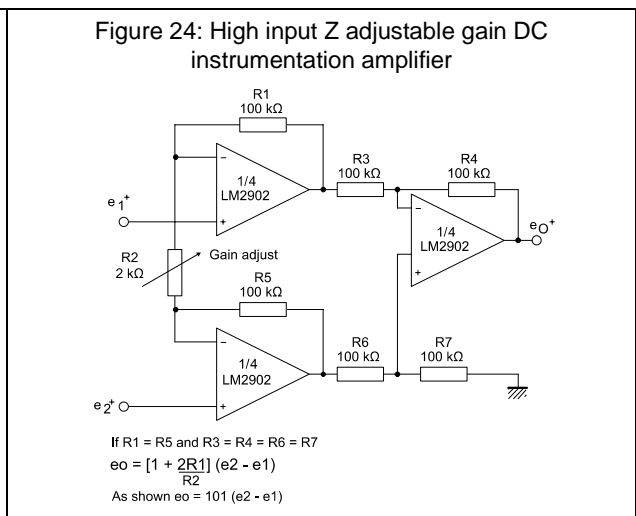
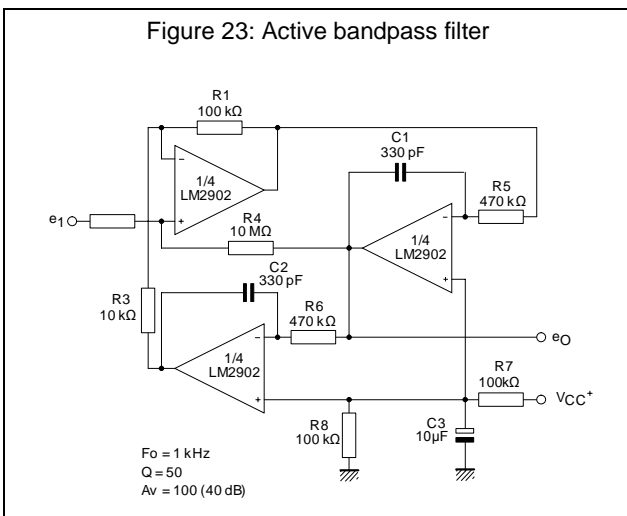
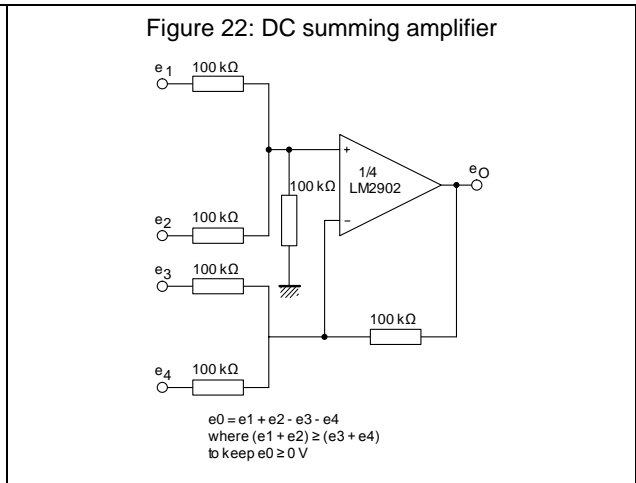
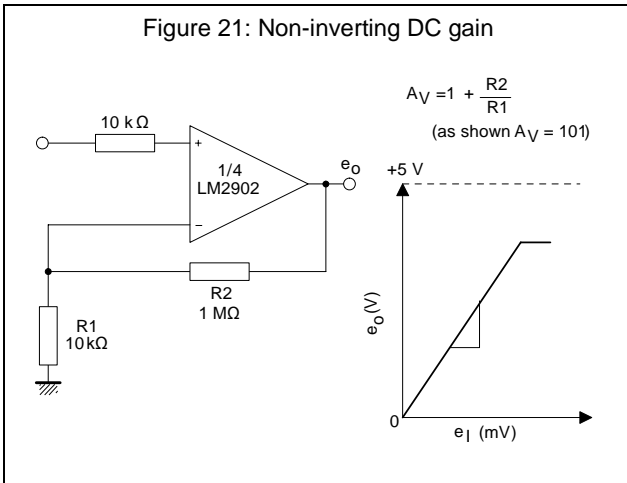
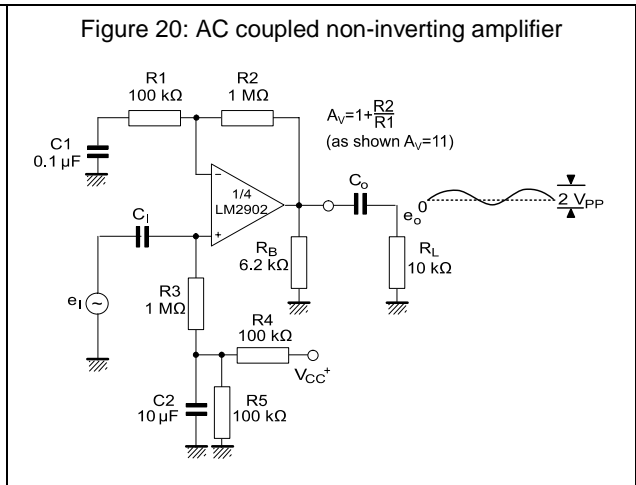
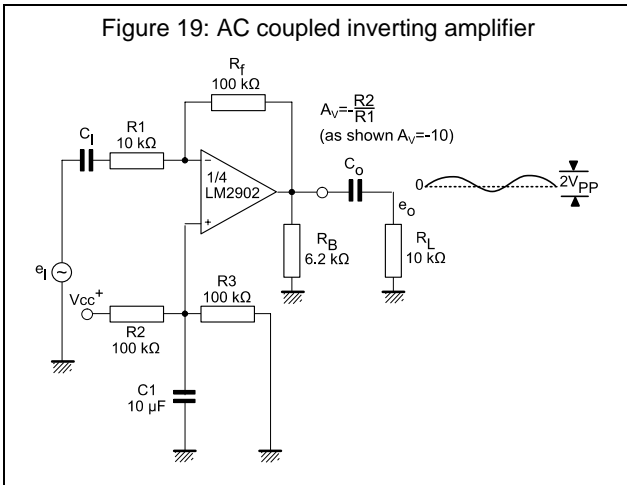


Figure 25: High input Z, DC differential amplifier

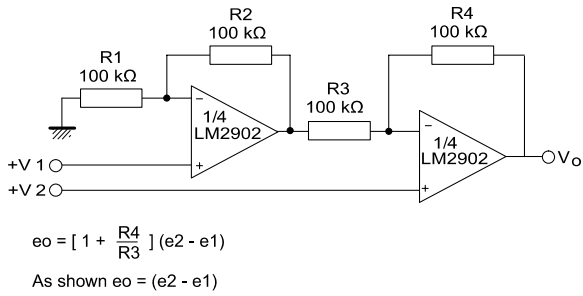


Figure 26: Low drift peak detector

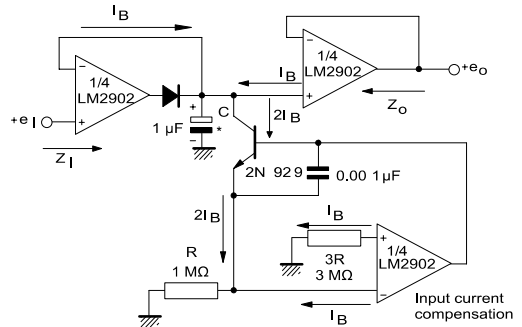
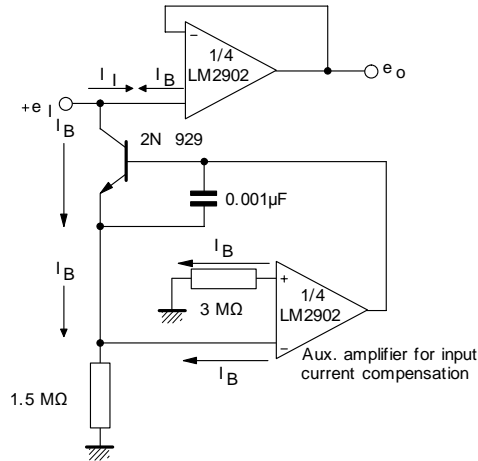


Figure 27: Using symmetrical amplifiers to reduce input current (general concept)



7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

7.1 SO14 package information

Figure 28: SO14 package outline

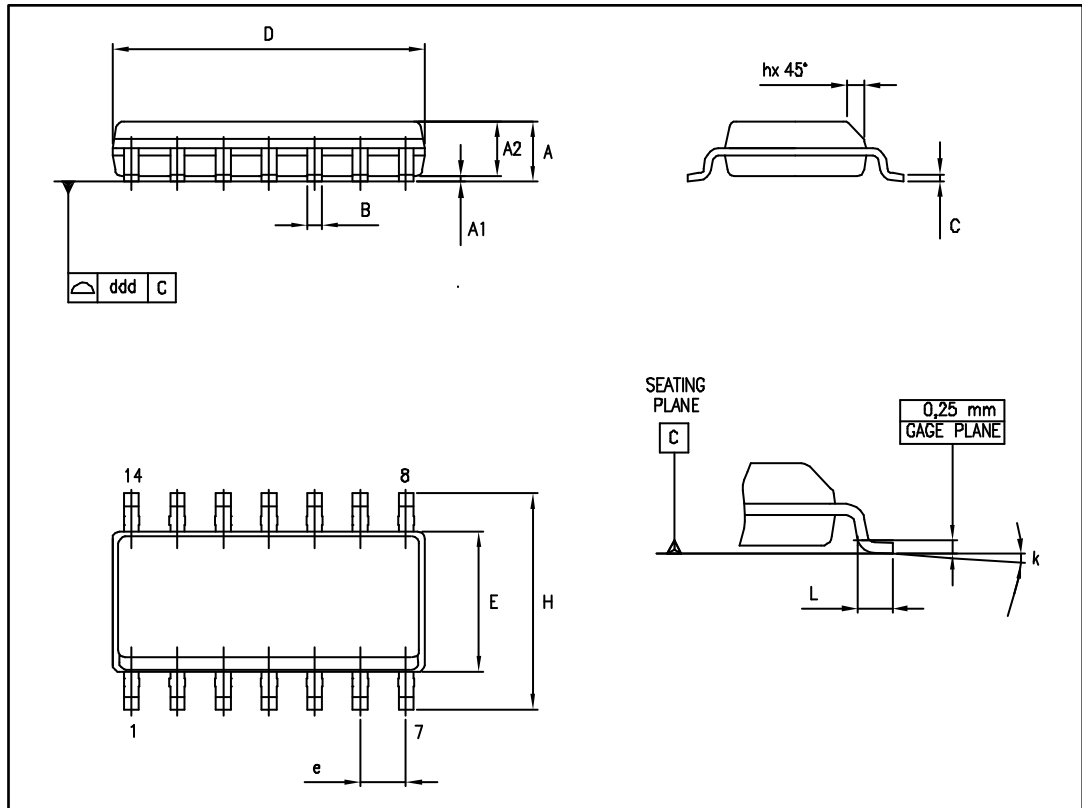


Table 4: SO14 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.35		1.75	0.05		0.068
A1	0.10		0.25	0.004		0.009
A2	1.10		1.65	0.04		0.06
B	0.33		0.51	0.01		0.02
C	0.19		0.25	0.007		0.009
D	8.55		8.75	0.33		0.34
E	3.80		4.0	0.15		0.15
e		1.27			0.05	
H	5.80		6.20	0.22		0.24
h	0.25		0.50	0.009		0.02
L	0.40		1.27	0.015		0.05
k	8° (max)					
ddd			0.10			0.004

7.2 TSSOP14 package information

Figure 29: TSSOP14 package outline

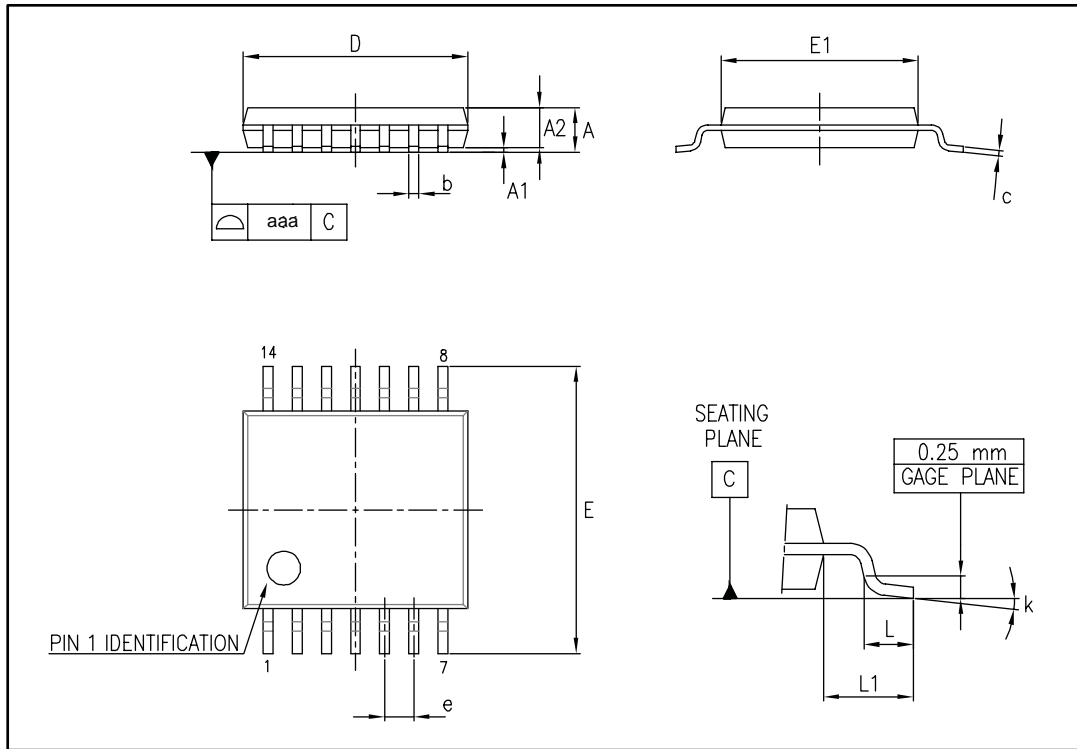


Table 5: TSSOP14 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.20			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.80	1.00	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.90	5.00	5.10	0.193	0.197	0.201
E	6.20	6.40	6.60	0.244	0.252	0.260
E1	4.30	4.40	4.50	0.169	0.173	0.176
e		0.65			0.0256	
L	0.45	0.60	0.75	0.018	0.024	0.030
L1		1.00			0.039	
k	0°		8°	0°		8°
aaa			0.10			0.004

7.3 QFN16 3x3 package information

Figure 30: QFN16 3x3 package outline

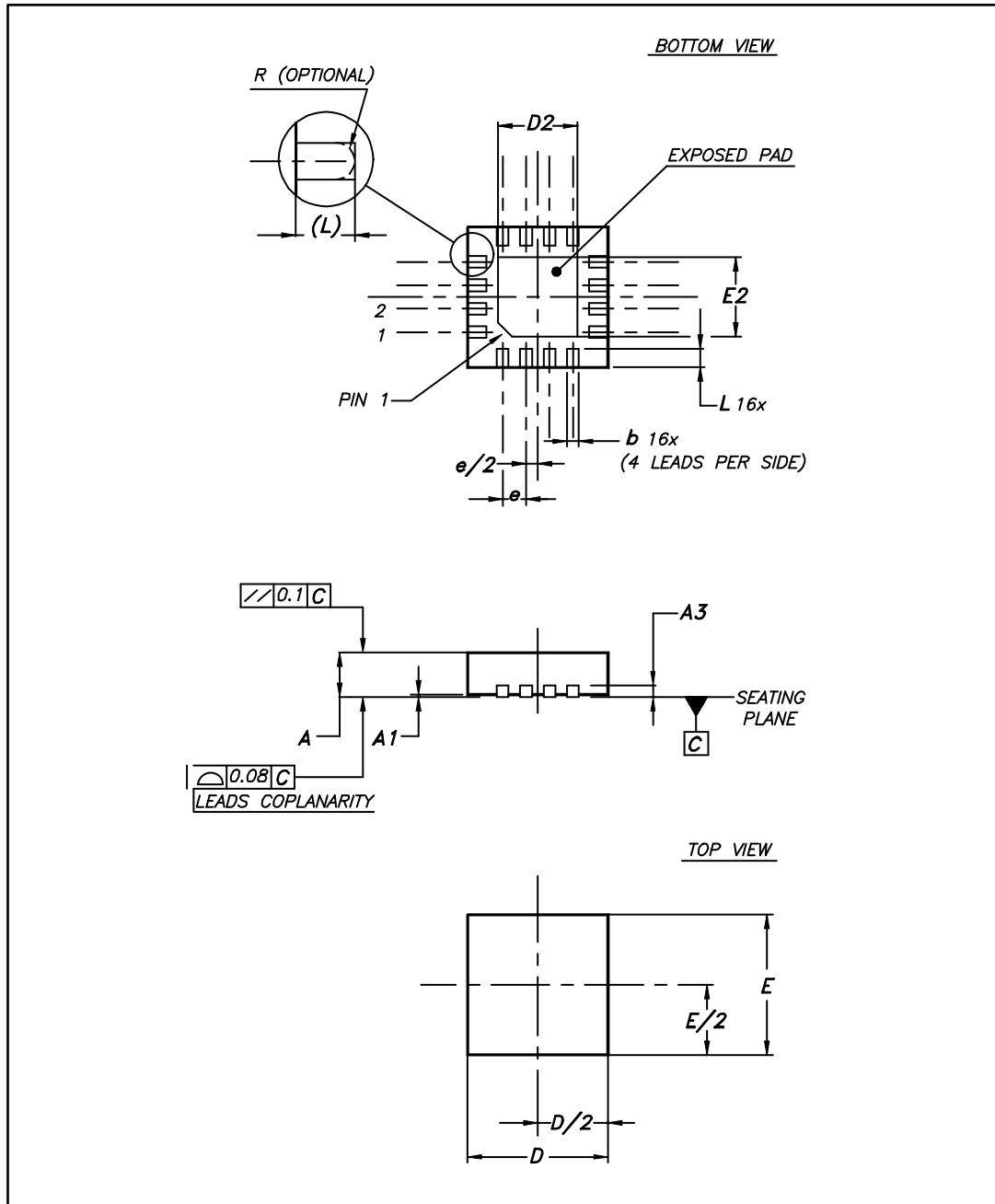
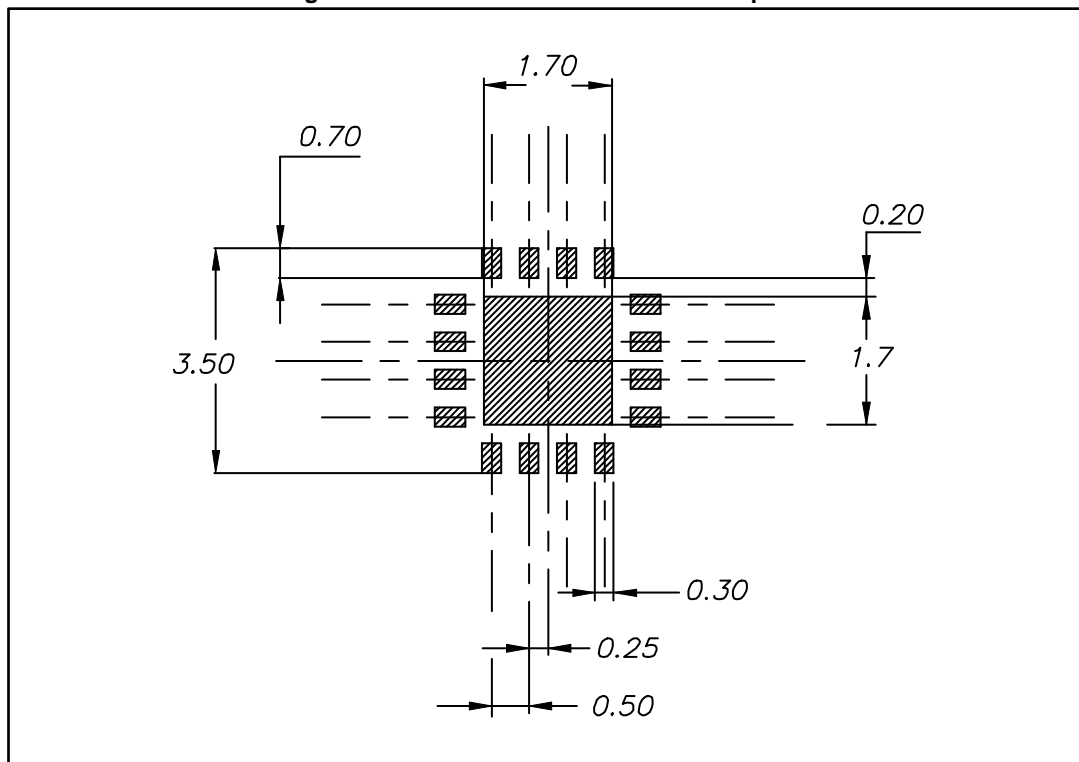


Table 6: QFN16 3x3 mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.80	0.90	1.00	0.031	0.035	0.039
A1	0		0.05	0		0.002
A3		0.20			0.008	
b	0.18		0.30	0.007		0.012
D	2.90	3.00	3.10	0.114	0.118	0.122
D2	1.50		1.80	0.059		0.071
E	2.90	3.00	3.10	0.114	0.118	0.122
E2	1.50		1.80	0.059		0.071
e		0.50			0.020	
L	0.30		0.50	0.012		0.020

Figure 31: QFN16 3x3 recommended footprint



8 Ordering information

Table 7: Order codes

Order code	Temperature range	Package	Packing	Marking
LM2902D	-40 ° C to 125 ° C	SO14	Tube or tape and reel	2902
LM2902DT		TSSOP14	Tape and reel	
LM2902PT		QFN16 3x3		K5H
LM2902Q4T		SO14, automotive grade level		2902Y
LM2902YDT ⁽¹⁾		TSSOP14, automotive grade level		
LM2902YPT ⁽¹⁾				

Notes:

⁽¹⁾Qualified and characterized according to AEC Q100 and Q003 or equivalent, advanced screening according to AEC Q001 & Q002 or equivalent.

9 Revision history

Table 8: Document revision history

Date	Revision	Changes
30-Nov-2001	1	Initial release.
01-Jul-2005	2	PPAP references inserted in the datasheet, see Table 3: Order codes. ESD protection inserted in Table 1 on page 4.
31-Oct-2005	3	An error in the device description was corrected on page 1. PPAP reference inserted in the datasheet see Table 3: Order codes. Minor grammatical and formatting changes throughout.
18-Jun-2007	4	Values for thermal resistance junction to ambient and ESD HBM corrected in Table 1: Absolute maximum ratings (AMR). Values for thermal resistance junction to case added in Table 1: Absolute maximum ratings (AMR). Table 2: Operating conditions added. Electrical characteristics figure captions updated. Section 6: Package information updated. Table 3: Order codes moved to end of document.
18-Dec-2007	5	Removed power dissipation parameter from AMR table and added maximum junction temperature. Updated footnotes for automotive grade order codes. Updated format of package information.
16-Feb-2012	6	Added AMR values for input current in Table 1 on page 4. Added QFN16 3 x 3 mm package information in Chapter 7: Ordering information. Removed LM2902YD order code from Table 3 and changed status of LM2902YPT order code.
29-Jan-2013	7	Small text/layout changes in Features and Description. Updated Figure 2: Pin connections (top view). Table 3: VCC+ = 5V, VCC- = Ground, V _o = 1.4V, T _{amb} = 25° C (unless otherwise specified): DV _{io} replaced by DV _{io} /DT. Replaced SO-14 package silhouette, package mechanical drawing (Figure 29) and package mechanical data (Table 5).
11-Jan-2017	8	Removed DIP package <i>Figure 1: "Schematic diagram (1/4 LM2902)"</i> : removed two diodes <i>Table 1: "Absolute maximum ratings (AMR)"</i> : updated value of V _{CC} Updated TSSOP14 package for L and aaa parameters

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Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9